

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	10/654240	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 17:33
S3	3	"6362090"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 18:42
S4	17839	((dielectric insulat\$3) with (trench via hole damascene groove aperture)) with mask\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:05
S5	9987	S4 and (dielectric insulat\$3) with (photoresist resist)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 18:45
S6	201	S5 and (dielectric insulat\$3) with (bond\$3 adj pad)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:05
S7	107	S6 and ('cu' copper interconnect\$3) with (bond\$3 adj pad)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:51
S8	3	"6452271"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:52
S9	4	"6445069"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:55
S10	6	"6444489"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:00
S11	1	"6424090"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:01

S12	17	"6153940"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:04
S13	17	"6153940"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:05
S14	39	"3986255"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:05
S15	16458	((bonding bond) near3 pad) with (substrate dielectric insulat\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:09
S16	6774	S15 and ((bonding bond) near3 pad) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:10
S17	343	S16 and ((mask\$3 photoresist resist) near3 pad) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:11
S18	124	S17 and ('cu' copper) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 08:34
S19	1	10/964019	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 08:34
S20	8707	(bond\$3 adj pad) with (trench via hole damascene groove aperture)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:14
S21	11037	(bond\$3 adj pad) with (trench via hole groove aperture damascene aperture opening recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:07
S22	4687	S21 and (dielectric insulat\$3) with (trench via hole groove aperture damascene aperture opening recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:07

S23	1966	S22 and (mask masking resist photoresist) with (trench via hole groove aperture damascene aperture opening recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:08
S24	1966	S23 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:09
S25	1755	S24 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with etch\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:10
S26	951	S25 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with ('cu' copper)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:11
S27	608	S26 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:11
S28	126	S26 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two different difference) near5 (part area region)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:12

S29	122	S27 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two different difference) near5 (part area region)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:12
S30	376	S27 and (bond\$3 adj pad) with (method process)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:14
S31	250	S27 and (bond\$3 adj pad) near5 (method process)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 15:42
S32	1	10/701423	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 12:38
S33	1	10/837528	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 12:38
S34	2	bond adj pad and first adj mask and second adj mask and contiguous.clm.	US-PGPU B	OR	ON	2005/09/21 15:45
S35	1	(bond adj pad and first adj mask and second adj mask and contiguous).clm.	US-PGPU B	OR	ON	2005/09/21 15:45